C1 and etching the at least one layer of organosilicate glass with the plasma from the etchant gas.

2. (Cancelled).

3. (Cancelled).

4. (Once Amended) The method, as recited in claim [3] 1, wherein the etchant gas mixture further comprises argon.

C2 5 & 7 5. (Once Amended) The method, as recited in claim 4, [further comprising etching] wherein the at least one layer of organosilicate glass is a first layer of organosilicate glass dielectric, which is etched with the plasma from the etchant gas comprising C4F8, CF4, CH2F2, oxygen and argon.

7. (Twice Amended) A method for etching a feature in an integrated circuit wafer, the method comprising:

C3 5 & 7 positioning the wafer in a reaction chamber;

etching through a first layer of organosilicate glass dielectric, comprising:

providing a flow of an etchant gas mixture including C4F8, CH2F2, oxygen, and CF4 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

8. (Cancelled).

9. (Cancelled).

C4 5 & 7 10. (Once Amended) The method, as recited in claim [9] 7, wherein the etchant gas mixture for etching through the first layer of organosilicate glass, further comprises argon.

11. (Once Amended) The method, as recited in claim 10, further comprising etching through an etch stop layer, comprising:

providing an etchant gas mixture without C4F8 and [CF4] CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

12. (Once Amended) The method, as recited in claim 10, further comprising etching through an etch stop layer after etching through the first layer of organosilicate glass, comprising:

Sub D1

stopping the flow of C4F8 and [CF4] CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

C4 und

13. (Once Amended) The method, as recited in claim 12, further comprising etching through a second layer of organosilicate glass dielectric, comprising:

restarting the flow of C4F8 and [CF4] CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

14. (Once Amended) The method, as recited in claim 13, further comprising stripping a photoresist mask, comprising:

stopping the flow of C4F8 and CF4 into the reaction chamber, after etching through the second layer of organosilicate glass;

providing a flow of nitrogen into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

19. (Cancelled).